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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

APPLICANT: B. Martinez-Tovar et al : GROUP ART UNIT: 3641  
SERIAL NO: 09/470,343 :  
FILING DATE: December 22, 1999 : EXAMINER: T. Chambers  
TITLE: TITANIUM SEMICONDUCTOR BRIDGE :  
IGNITER : ATTY. DKT.: P-1583

**RESPONSE TO OFFICE ACTION**

Commissioner for Patents  
Box RCE  
Washington, DC 20231

January 25, 2002  
**RECEIVED**

FEB 27 2002

**GROUP 3600**

Dear Sir:

This paper is responsive to the office action mailed September 25, 2001 in the captioned application.

**AMENDMENTS**

**In The Specification**

Amend the paragraph at page 2, lines 6-14 to read as follows.

In accordance with the present invention there is provided a titanium semiconductor bridge device comprising a substrate and an electrical bridge structure disposed on the substrate. The bridge structure comprises a layer of a material having a negative coefficient of electrical conductivity at temperatures above ambient temperature and having disposed thereover a layer consisting essentially of titanium, the bridge structure comprising a bridge section extending between and connecting spaced-apart pad sections, each pad section being of larger area than the bridge section. A pair of electrically conductive lands each overlies a respective one of the pad sections and is spaced apart from the other land to leave the bridge section exposed.

Amend the paragraph at page 2, line 31 through page 3, line 3 as follows.